

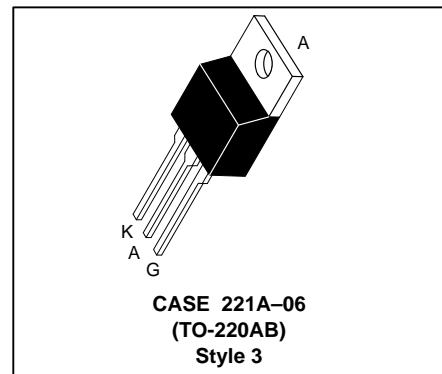
Silicon Controlled Rectifiers Reverse Blocking Thyristors

**MCR16
SERIES***
*Motorola preferred devices

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability — 160 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity

SCRs
16 AMPERES RMS
400 thru 800
VOLTS



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|------------------------|-------------------|------------------------|
| Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage ($T_J = -40$ to 125°C) | V_{DRM} V_{RRM} | 400 600 800 | Volts |
| On-State RMS Current (All Conduction Angles) | $I_T(\text{RMS})$ | 16 | A |
| Peak Non-repetitive Surge Current (One Half Cycle, 60 Hz, $T_J = 125^\circ\text{C}$) | I_{TSM} | 160 | A |
| Circuit Fusing Consideration ($t = 8.3$ ms) | I^2t | 106 | A^2sec |
| Peak Gate Power (Pulse Width ≤ 1.0 μs , $T_C = 80^\circ\text{C}$) | P_{GM} | 5.0 | Watts |
| Average Gate Power ($t = 8.3$ ms, $T_C = 80^\circ\text{C}$) | $P_{G(AV)}$ | 0.5 | Watts |
| Peak Gate Current (Pulse Width ≤ 1.0 μs , $T_C = 80^\circ\text{C}$) | I_{GM} | 2.0 | A |
| Operating Junction Temperature Range | T_J | -40 to +125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -40 to +150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| | | | |
|---|------------------------------------|-------------|--------------------|
| Thermal Resistance — Junction to Case — Junction to Ambient | $R_{\theta JC}$ $R_{\theta JA}$ | 1.5 62.5 | $^\circ\text{C/W}$ |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | T_L | 260 | $^\circ\text{C}$ |

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

MCR16 SERIES

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|------------------------|------------------|---|---|------|----|
| Peak Forward Blocking Current | T _J = 25°C | I _{DRM} | — | — | 0.01 | mA |
| Peak Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM} , Gate Open) | T _J = 125°C | I _{RRM} | — | — | 2.0 | mA |

ON CHARACTERISTICS

| | | | | | |
|--|-----------------|-----|------|-----|-------|
| Peak On-State Voltage* (I _{TM} = 32 A) | V _{TM} | — | — | 1.7 | Volts |
| Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 100 Ω) | I _{GT} | 2.0 | 8.0 | 20 | mA |
| Gate Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 100 Ω) | V _{GT} | 0.5 | 0.65 | 1.0 | Volts |
| Hold Current (Anode Voltage = 12 V) | I _H | 4.0 | 25 | 40 | mA |

DYNAMIC CHARACTERISTICS

| | | | | | |
|--|-------|----|-----|---|------|
| Critical Rate of Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 25°C) | dv/dt | 50 | 200 | — | V/μs |
|--|-------|----|-----|---|------|

*Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

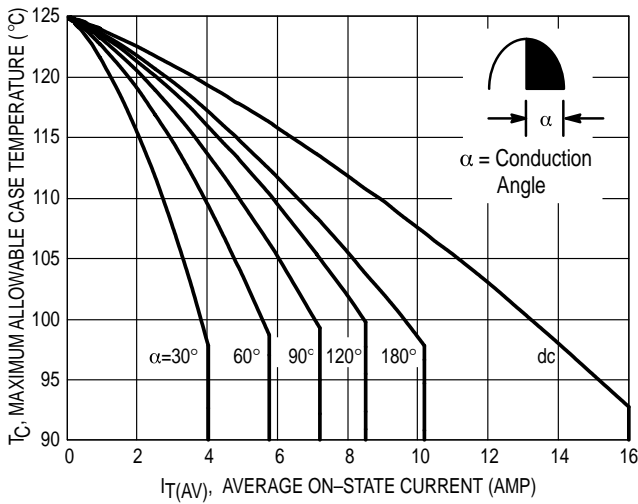


Figure 1. Average Current Derating

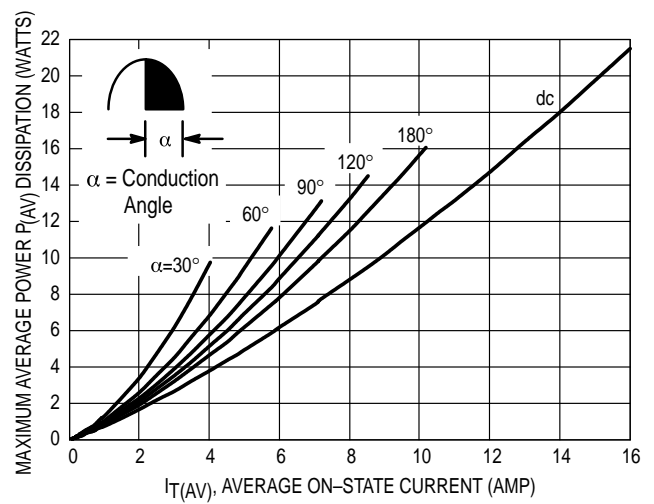


Figure 2. Maximum On-State Power Dissipation

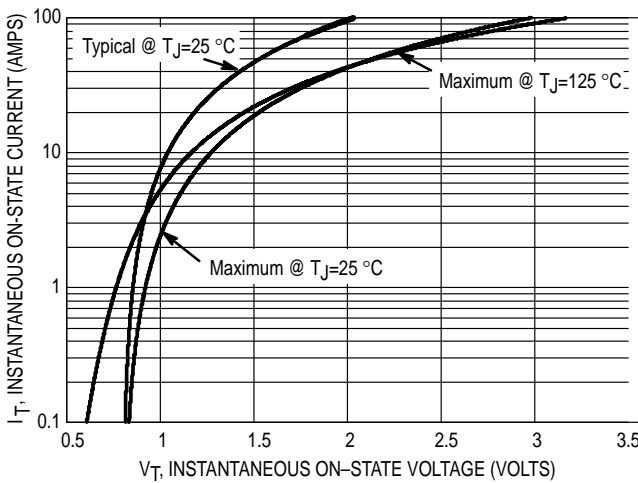


Figure 3. On-State Characteristics

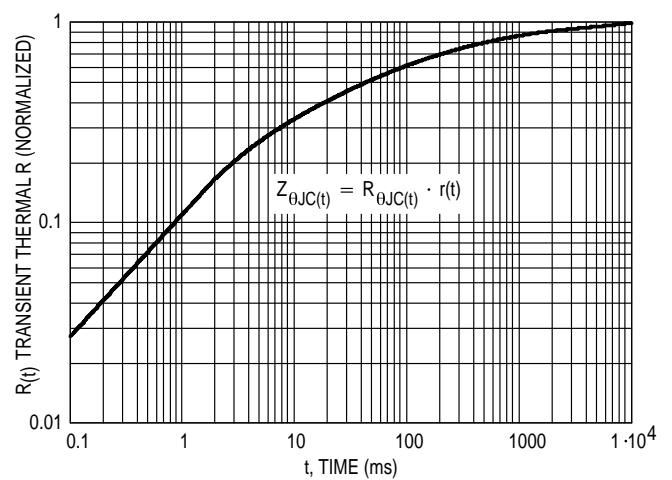


Figure 4. Transient Thermal Response

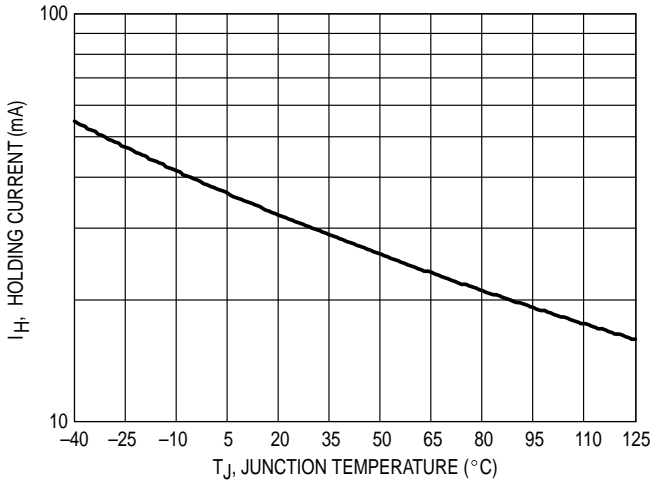


Figure 5. Typical Holding Current Versus Junction Temperature

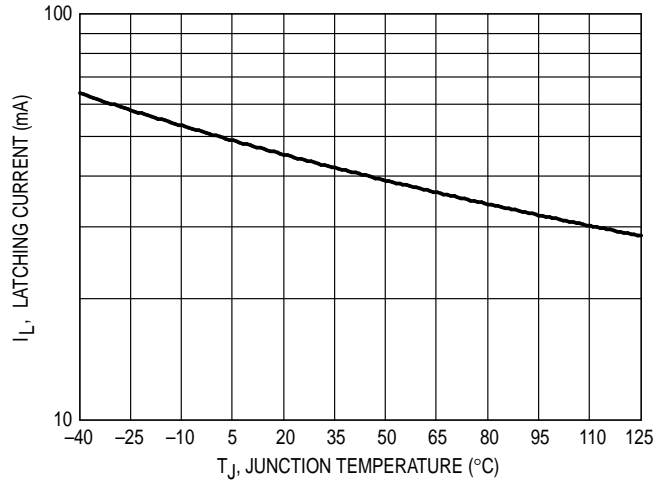


Figure 6. Typical Latching Current Versus Junction Temperature

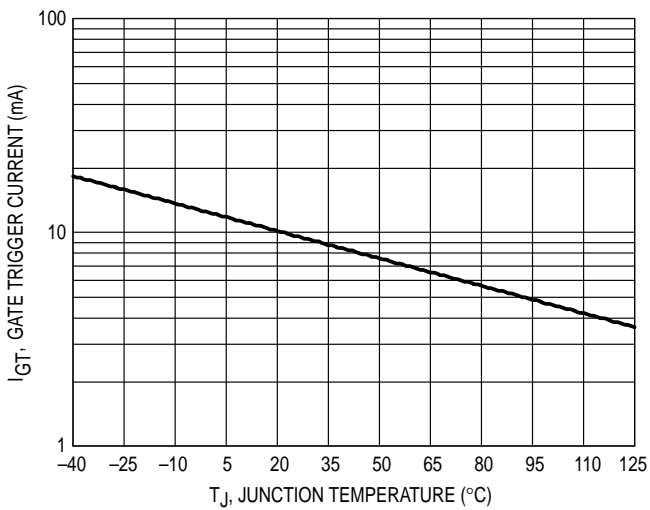


Figure 7. Typical Gate Trigger Current Versus Junction Temperature

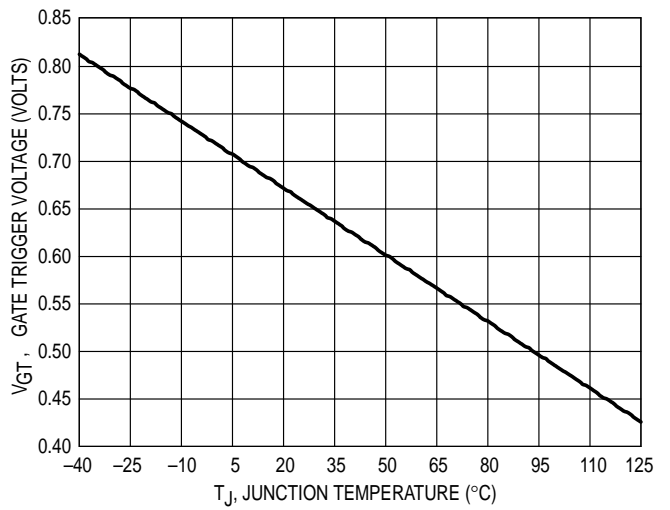


Figure 8. Typical Gate Trigger Voltage Versus Junction Temperature

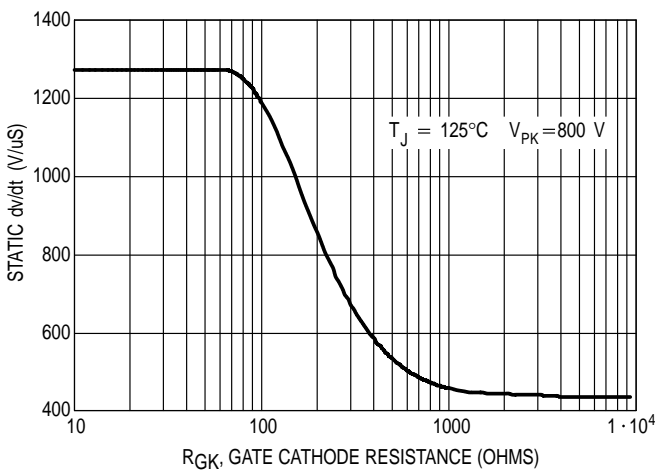


Figure 9. Typical Exponential Static dv/dt Versus Gate Cathode Resistance.

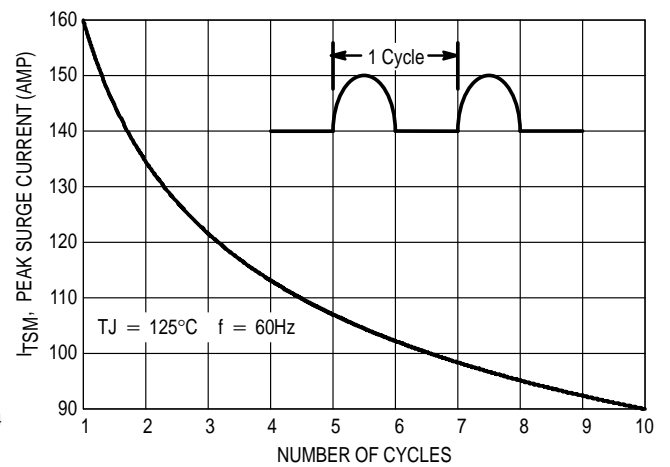
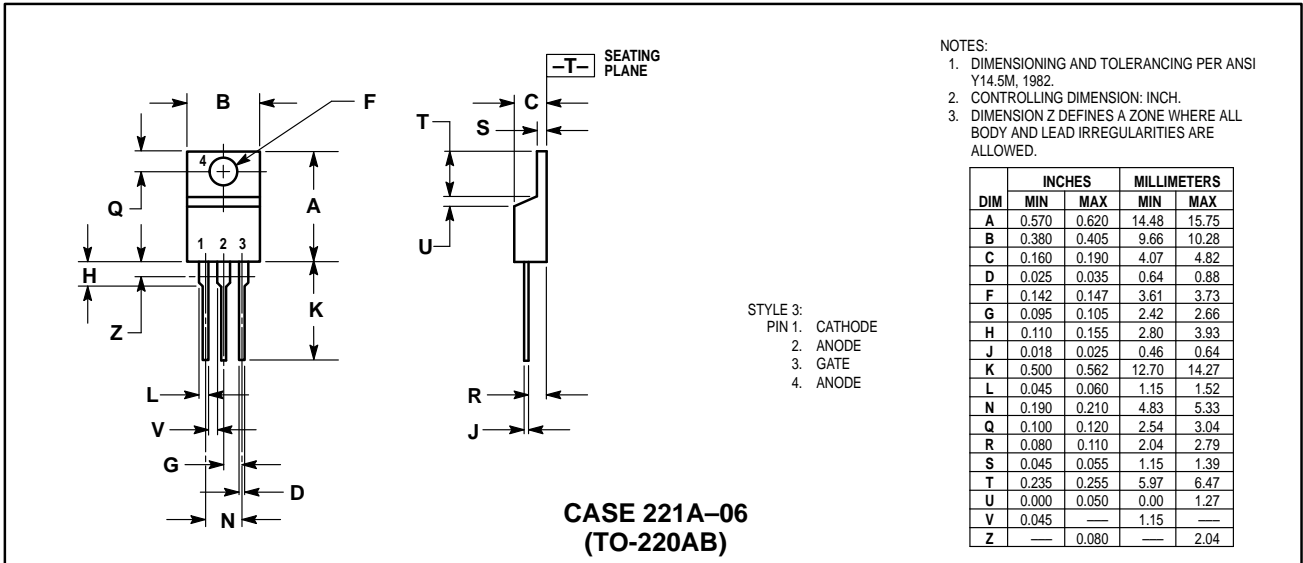


Figure 10. Maximum Non-Repetitive Surge Current

MCR16 SERIES

PACKAGE DIMENSIONS



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